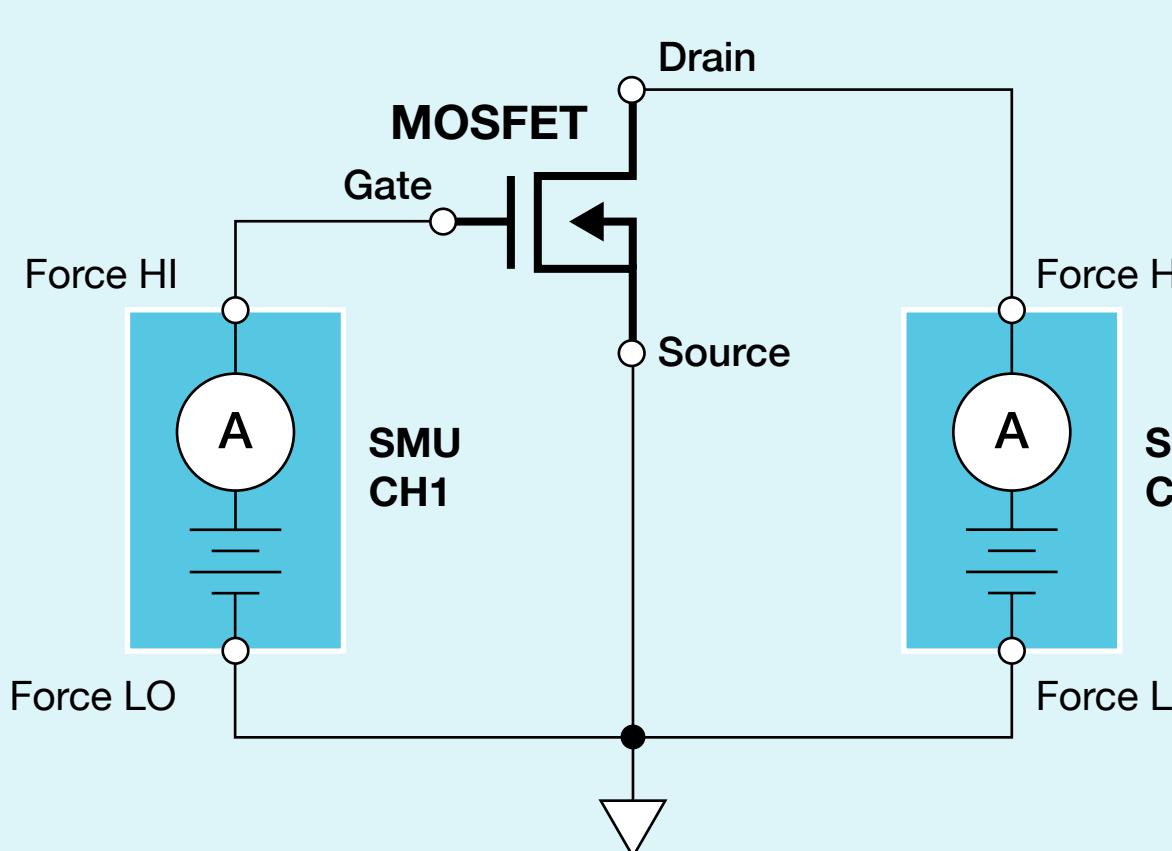
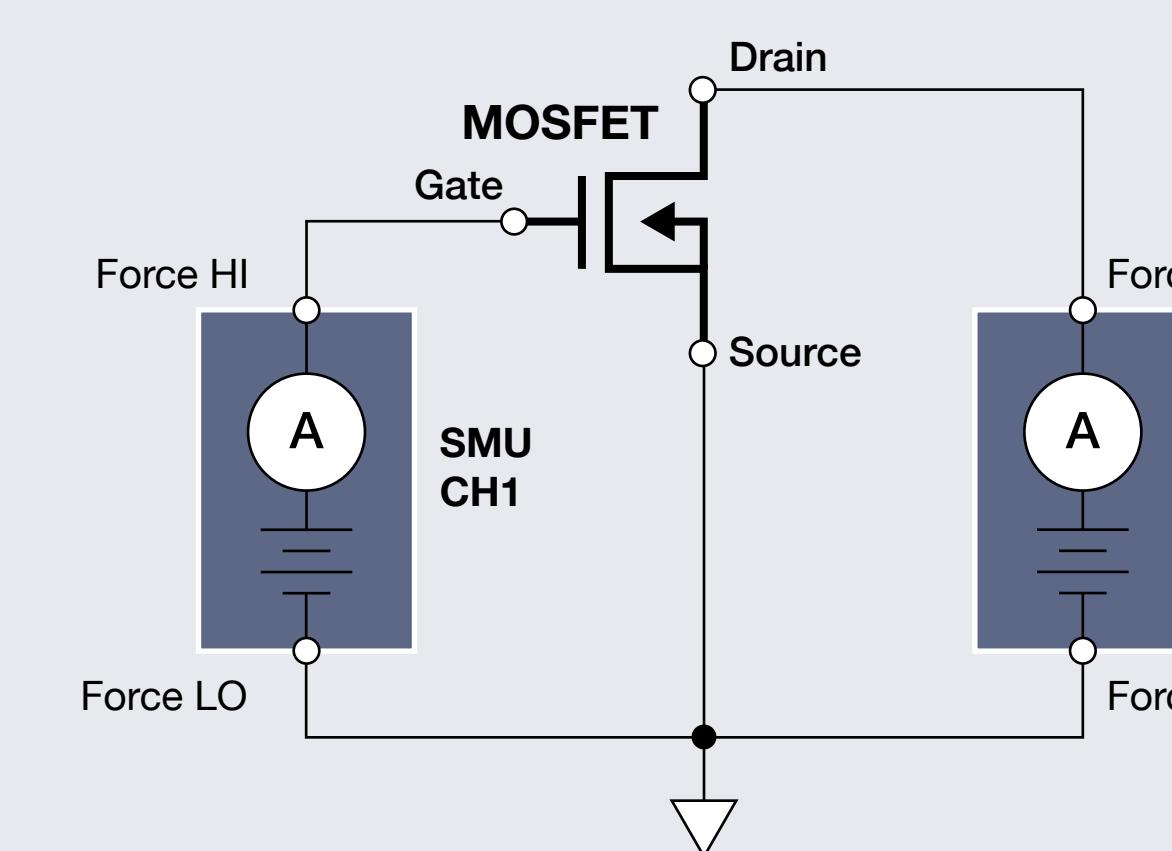
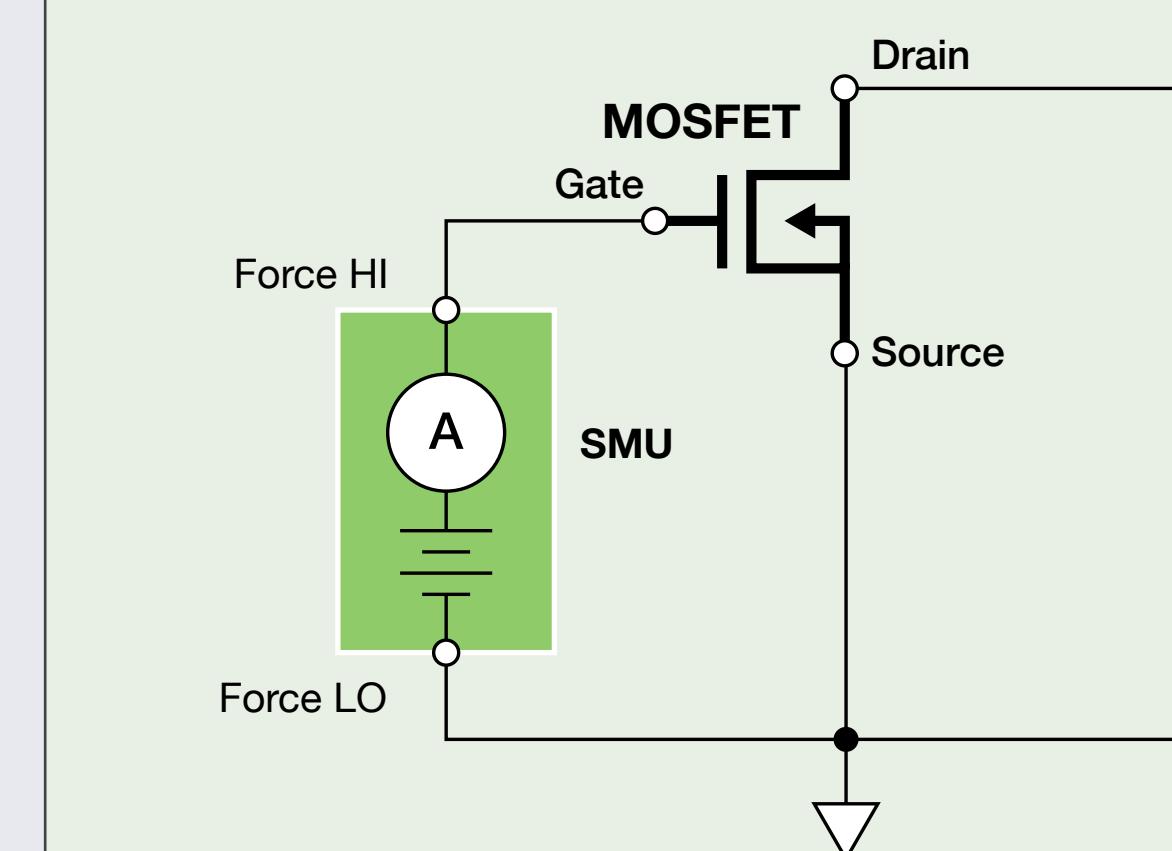
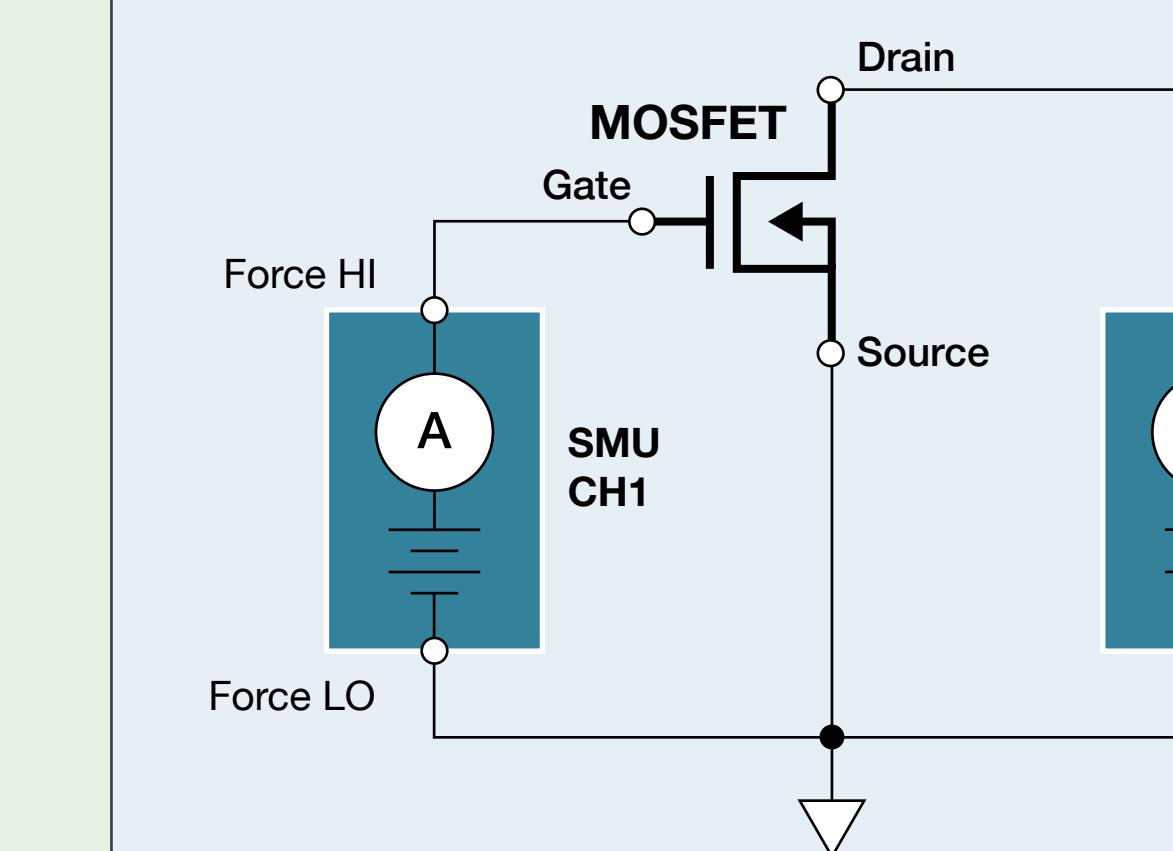
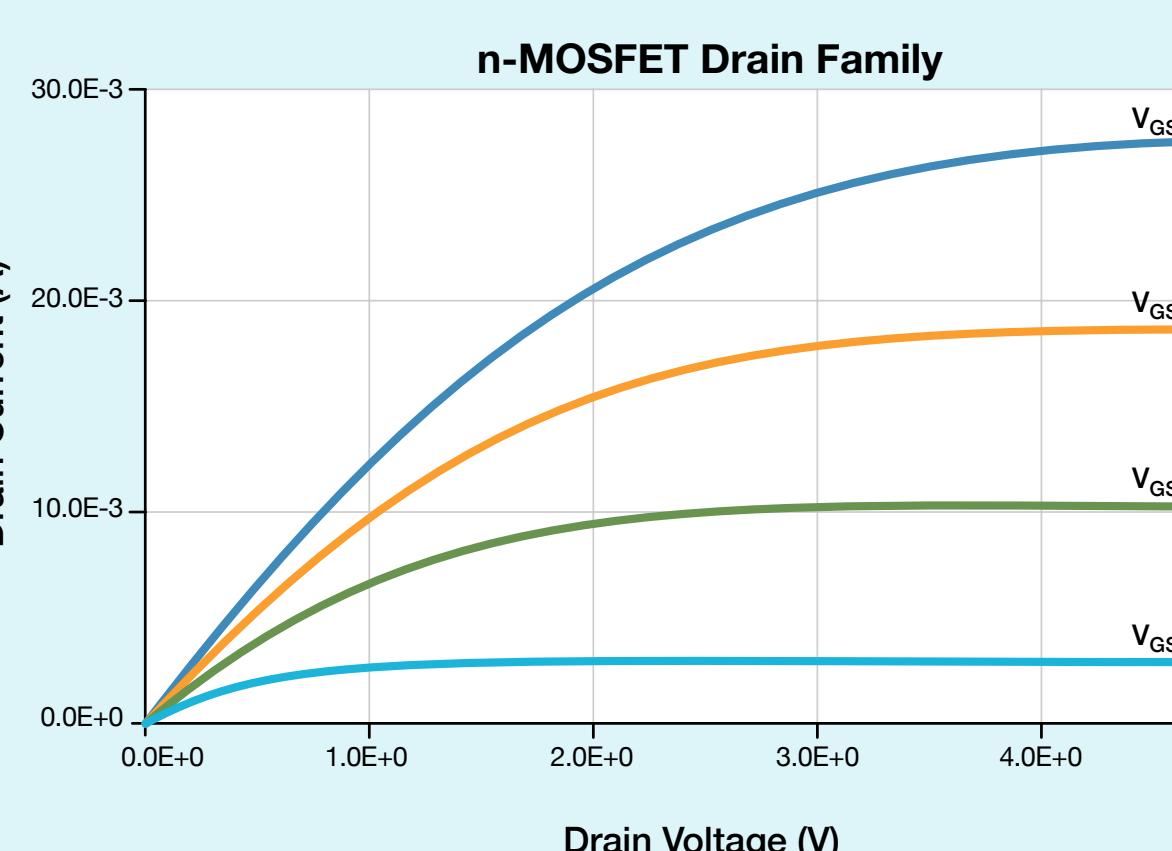
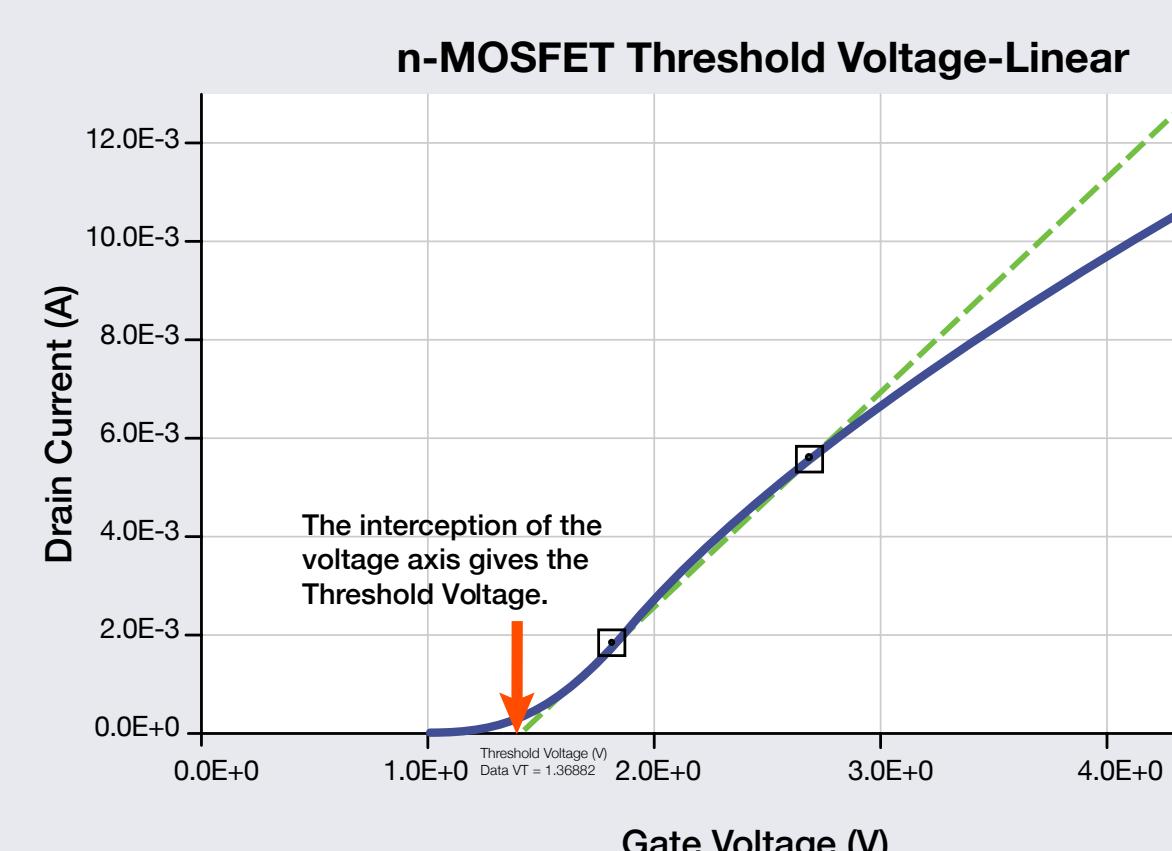
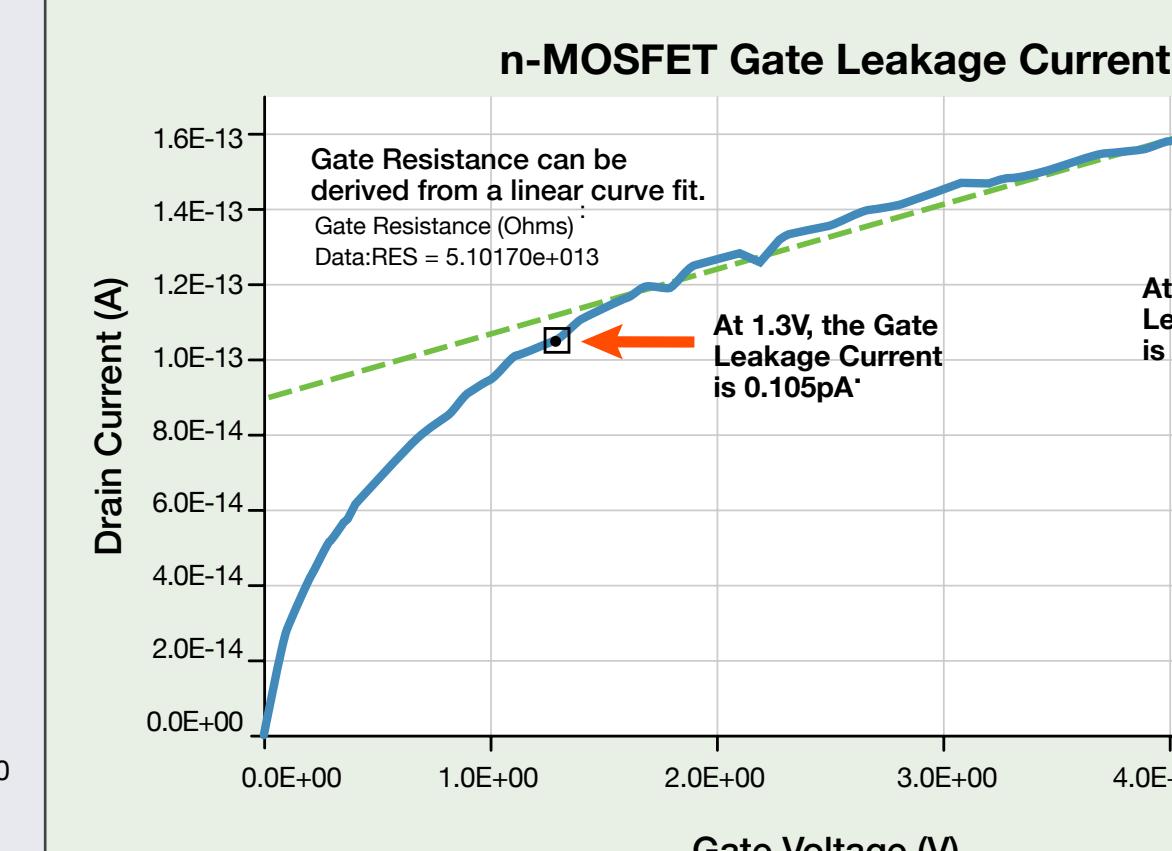
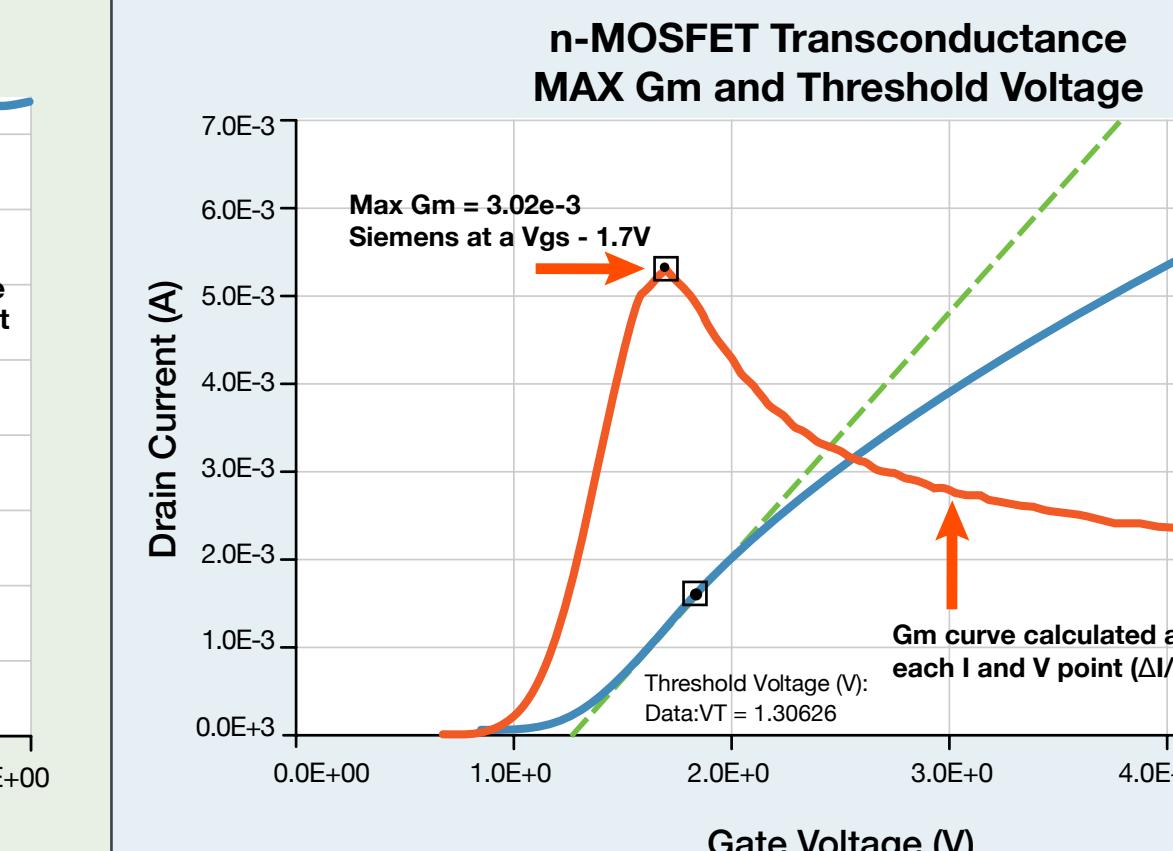


FOUR KEY TESTS: Validating MOSFET Performance in Power Supply Designs

TEST SPECIFICATIONS	Drain Family of Curves	Threshold Voltage	Gate Leakage	Transconductance
	<p>Definition: Transistor output characteristics plotted as I_{DS} versus V_{DS} for several values of V_{GS}.</p> <p>Measurement Parameter: I_{DS} vs. V_{DS}</p> <p>Importance in Device Selection: By looking at these curves, the designer can determine the best operating point for the application. At low drain-source voltages, the MOSFET behaves like a variable resistance whose value is controlled by the applied gate-source voltage. At higher drain-source voltages, the MOSFET passes a current whose value depends on the applied gate-source voltage. In most circuits, it is used in this 'high voltage' region and acts as a voltage-controlled current source.</p> <p>Test Technique:</p> <ol style="list-style-type: none"> Step the gate voltage (V_{GS}) across the desired range of values at specified increments. At each V_{GS} value, V_{DS} is swept across the desired V_{DS} range. Measure the drain-source current (I_{DS}) at each V_{DS} increment. 	<p>Definition: The minimum gate-to-source voltage differential required to produce current flow from the source to drain.</p> <p>Measurement Parameter: V_{TH}</p> <p>Importance in Device Selection: Threshold voltage is important for determining the on-state and the off-state of the MOSFET. $V_{GS(th)}$ is defined where $V_{DS} = V_{GS}$, although it is sometimes quoted for a fixed V_{DS} (e.g. 10 V.)</p> <p>Test Technique:</p> <ol style="list-style-type: none"> Sweep the gate voltage (V_{GS}) while the drain-source voltage (V_{DS}) is set to a particular value. Measure the drain current (I_D) at each value incremental of V_{GS} in the sweep. Determine the threshold voltage (V_{TH}) through a linear curve fit. A linear region on the curve is selected. The interception of the voltage axis gives the threshold voltage. 	<p>Definition: Transistor gate leakage current as a function of the gate voltage.</p> <p>Measurement Parameter: I_G vs. V_G</p> <p>Importance in Device Selection: The gate leakage current is important when calculating how much current is required to keep the device turned on. Because it is a leakage current through an insulator, this current is independent of temperature.</p> <p>Test Technique:</p> <ol style="list-style-type: none"> Sweep the gate voltage (V_G) over the desired range while the drain and source are tied to common. Measure the gate current (I_G). 	<p>Definition: The change in the drain current divided by the small change in the gate/source voltage with a constant drain/source voltage.</p> <p>Measurement Parameter: I_D vs. V_{GS}</p> <p>Importance in Device Selection: Transconductance helps the engineer to choose the best MOSFET with the right amount of gain (amplification) for the designs.</p> <p>Test Technique:</p> <ol style="list-style-type: none"> Sweep the gate voltage (V_{GS}) over the desired range, while maintaining a constant drain/source voltage (V_{DS}). Measure the drain current (I_D) at each increment step of V_{GS}. Calculate transconductance (g_m) by dividing the small changes in I_D by the small changes in V_{GS}. $g_m = \Delta I_D / \Delta V_{GS}$.
TEST CONFIGURATION				
TYPICAL RESULTS	<p>n-MOSFET Drain Family</p> 	<p>n-MOSFET Threshold Voltage-Linear</p> 	<p>n-MOSFET Gate Leakage Current</p> 	<p>n-MOSFET Transconductance MAX Gm and Threshold Voltage</p> 



Four Key Tests for Validating MOSFET Performance in Power Supply Designs

POSTER

Contact Information:
 Balkans, Israel, South Africa and other ISS Countries: +41 52 675 3777
 Australia 1 800 759 465
 Austria 0800 2255 4835
 Belgium 0800 2255 4835
 Brazil +55 (11) 3759 7627
 Canada 1 800 833 9200
 Central Europe / Baltics +41 52 675 3777
 Central Europe / Greece +41 52 675 3777
 Denmark +45 80 88 3401
 Finland +41 52 675 3777
 France 0800 2255 4835
 Germany 0800 2255 4835
 Hong Kong 1 800 829 5835
 India 000 000 650 1835
 Indonesia 007 803 601 5249
 Italy 0800 2255 4835
 Japan 81 (3) 6714 3010
 Luxembourg +41 52 675 3777
 Mexico, Central/South America and Caribbean 52 (55) 56 04 50 90
 Middle East, Asia, and North Africa +41 52 675 3777
 The Netherlands 0800 2255 4835
 Norway 1 800 600 1238
 New Zealand 1 800 600 1238
 People's Republic of China 1 800 829 5835
 Philippines +800 1601 0077
 Poland +41 52 675 3777
 Portugal 80 081 12370
 Republic of Korea +82 2 9811 5000
 Russia CIS +7 950 6647764
 Singapore 1 800 601 1273
 South Africa +41 52 675 3777
 Spain 0800 2255 4835
 Sweden 0800 2255 4835
 Switzerland 0800 2255 4835
 Taiwan 886 (2) 2655 6888
 Thailand 1 800 011 1931
 United Kingdom / Ireland 0800 2255 4835
 USA 1 800 833 9200
 Vietnam 1 2090128

* European toll-free number. If not accessible, call: +41 52 675 3777

For More Information:

Vicom Australia

Grid Floor, 60 Grafton Road

Auckland 1010

New Zealand

+64 9 379 4596

info@vicom.co.nz

www.vicom.com.au

For More Information:

Vicom

Locating the way in test and measurement

Find more valuable resources at TEK.COM
 Copyright © Tektronix. All rights reserved. Reference products are covered by U.S. and foreign patents, issued and pending. Information in this publication supersedes that in all previously published material. Specifications and price changes reserved. TEKTRONIX and TEK are registered trademarks of Tektronix, Inc. All other trade names referenced are the service marks, trademarks or registered trademarks of their respective companies.
 03-30-16 KI-TKV-0615-0